

Features

- High speed
 - $t_{AA} = 8 \text{ ns}$
- Low active power
 - $I_{CC} = 225 \text{ mA}$ at 8 ns
- Low CMOS standby power
 - $I_{SB2} = 25 \text{ mA}$
- Operating voltages of $3.3 \pm 0.3\text{V}$
- 2.0V data retention
- Automatic power down when deselected
- TTL compatible inputs and outputs
- Available in Pb-free standard 119-Ball PBGA

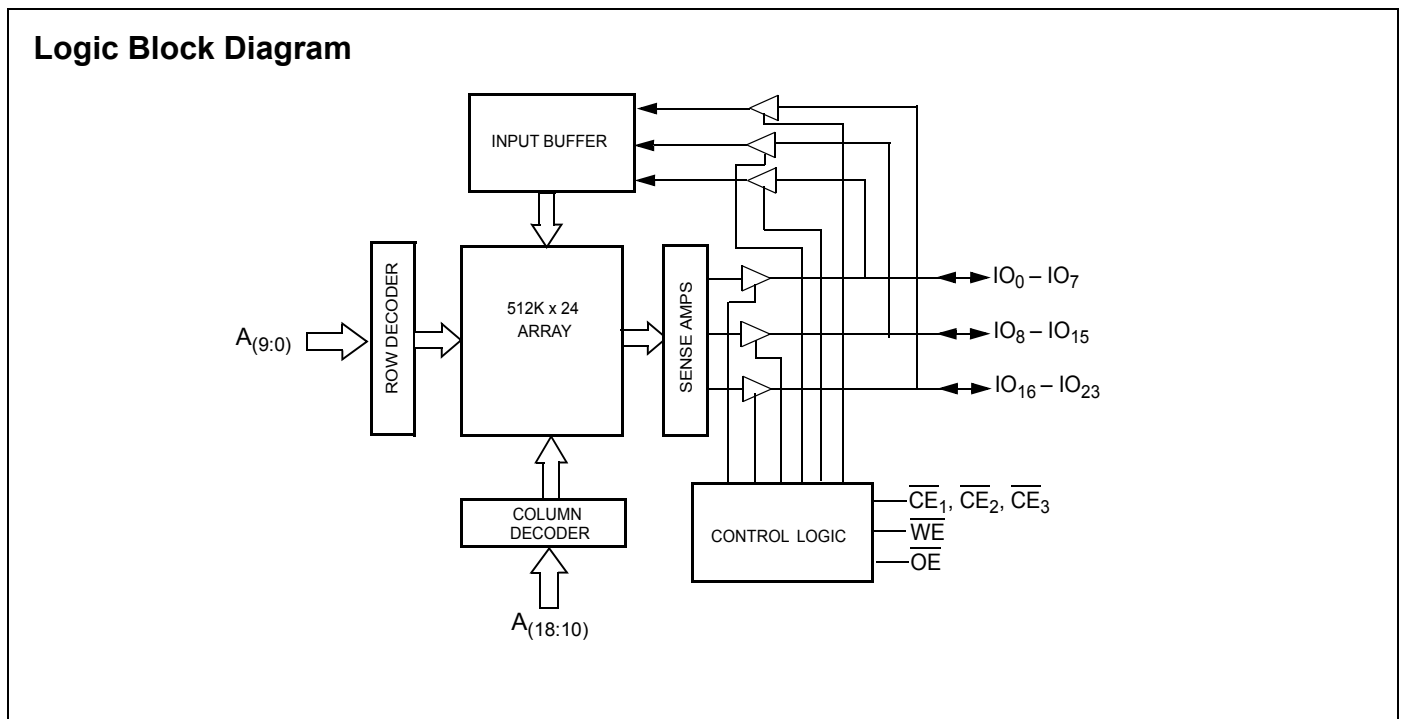
Functional Description

The CY7C1012DV33 is a high performance CMOS static RAM organized as 512K words by 24 bits. Each data byte is separately controlled by the individual chip selects (\overline{CE}_1 , \overline{CE}_2 , and \overline{CE}_3). \overline{CE}_1 controls the data on the $IO_0 - IO_7$, while \overline{CE}_2 controls the data on $IO_8 - IO_{15}$, and \overline{CE}_3 controls the data on the data pins $IO_{16} - IO_{23}$. This device has an automatic power down feature that significantly reduces power consumption when deselected.

Writing the data bytes into the SRAM is accomplished when the chip select controlling that byte is LOW and the write enable input (WE) input is LOW. Data on the respective input and output (IO) pins is then written into the location specified on the address pins ($A_0 - A_{18}$). Asserting all of the chip selects LOW and write enable LOW writes all 24 bits of data into the SRAM. Output enable (OE) is ignored while in WRITE mode.

Data bytes are also individually read from the device. Reading a byte is accomplished when the chip select controlling that byte is LOW and write enable (WE) HIGH, while output enable (OE) remains LOW. Under these conditions, the contents of the memory location specified on the address pins appear on the specified data input and output (IO) pins. Asserting all the chip selects LOW reads all 24 bits of data from the SRAM.

The 24 IO pins ($IO_0 - IO_{23}$) are placed in a high impedance state when all the chip selects are HIGH or when the output enable (\overline{OE}) is HIGH during a READ mode. For more information, see the [Truth Table](#) on page 8.



Selection Guide

	-8	Unit
Maximum Access Time	8	ns
Maximum Operating Current	225	mA
Maximum CMOS Standby Current	25	mA

Pin Configurations
Figure 1. 119-Ball PBGA (Top View) ^[1]

	1	2	3	4	5	6	7
A	NC	A	A	A	A	A	NC
B	NC	A	A	\overline{CE}_1	A	A	NC
C	IO ₁₂	NC	\overline{CE}_2	NC	\overline{CE}_3	NC	IO ₀
D	IO ₁₃	V _{DD}	V _{SS}	V _{SS}	V _{SS}	V _{DD}	IO ₁
E	IO ₁₄	V _{SS}	V _{DD}	V _{SS}	V _{DD}	V _{SS}	IO ₂
F	IO ₁₅	V _{DD}	V _{SS}	V _{SS}	V _{SS}	V _{DD}	IO ₃
G	IO ₁₆	V _{SS}	V _{DD}	V _{SS}	V _{DD}	V _{SS}	IO ₄
H	IO ₁₇	V _{DD}	V _{SS}	V _{SS}	V _{SS}	V _{DD}	IO ₅
J	NC	V _{SS}	V _{DD}	V _{SS}	V _{DD}	V _{SS}	NC
K	IO ₁₈	V _{DD}	V _{SS}	V _{SS}	V _{SS}	V _{DD}	IO ₆
L	IO ₁₉	V _{SS}	V _{DD}	V _{SS}	V _{DD}	V _{SS}	IO ₇
M	IO ₂₀	V _{DD}	V _{SS}	V _{SS}	V _{SS}	V _{DD}	IO ₈
N	IO ₂₁	V _{SS}	V _{DD}	V _{SS}	V _{DD}	V _{SS}	IO ₉
P	IO ₂₂	V _{DD}	V _{SS}	V _{SS}	V _{SS}	V _{DD}	IO ₁₀
R	IO ₂₃	A	NC	NC	NC	A	IO ₁₁
T	NC	A	A	\overline{WE}	A	A	NC
U	NC	A	A	\overline{OE}	A	A	NC

Note

1. NC pins are not connected on the die.

Maximum Ratings

Exceeding maximum ratings may shorten the useful life of the device. These user guidelines are not tested.

- Storage Temperature -65°C to +150°C
- Ambient Temperature with Power Applied -55°C to +125°C
- Supply Voltage on V_{CC} Relative to GND ^[2] -0.5V to +4.6V
- DC Voltage Applied to Outputs in High-Z State ^[2] -0.5V to V_{CC} + 0.5V
- DC Input Voltage ^[2] -0.5V to V_{CC} + 0.5V

- Current into Outputs (LOW) 20 mA
- Static Discharge Voltage..... >2001V (MIL-STD-883, Method 3015)
- Latch Up Current >200 mA

Operating Range

Range	Ambient Temperature	V _{CC}
Commercial	0°C to +70°C	3.3V ± 0.3V

DC Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions ^[3]	-8		Unit
			Min	Max	
V _{OH}	Output HIGH Voltage	V _{CC} = Min, I _{OH} = -4.0 mA	2.4		V
V _{OL}	Output LOW Voltage	V _{CC} = Min, I _{OL} = 8.0 mA		0.4	V
V _{IH}	Input HIGH Voltage		2.0	V _{CC} + 0.3	V
V _{IL} ^[2]	Input LOW Voltage		-0.3	0.8	V
I _{IX}	Input Leakage Current	GND ≤ V _I ≤ V _{CC}	-1	+1	μA
I _{OZ}	Output Leakage Current	GND ≤ V _{OUT} ≤ V _{CC} , output disabled	-1	+1	μA
I _{CC}	V _{CC} Operating Supply Current	V _{CC} = Max, f = f _{MAX} = 1/t _{RC} I _{OUT} = 0 mA CMOS levels		225	mA
I _{SB1}	Automatic CE Power Down Current — TTL Inputs	Max V _{CC} , $\overline{CE} \geq V_{IH}$ V _{IN} ≥ V _{IH} or V _{IN} ≤ V _{IL} , f = f _{MAX}		30	mA
I _{SB2}	Automatic CE Power Down Current — CMOS Inputs	Max V _{CC} , $\overline{CE} \geq V_{CC} - 0.3V$, V _{IN} ≥ V _{CC} - 0.3V, or V _{IN} ≤ 0.3V, f = 0		25	mA

Notes

- 2. V_{IL} (min) = -2.0V and V_{IH}(max) = V_{CC} + 2V for pulse durations of less than 20 ns.
- 3. CE indicates a combination of all three chip enables. When active LOW, CE indicates the \overline{CE}_1 , \overline{CE}_2 , and \overline{CE}_3 LOW. When HIGH, CE indicates the \overline{CE}_1 , \overline{CE}_2 , or \overline{CE}_3 is HIGH.

Capacitance

Tested initially and after any design or process changes that may affect these parameters.

Parameter	Description	Test Conditions	Max	Unit
C _{IN}	Input Capacitance	T _A = 25°C, f = 1 MHz, V _{CC} = 3.3V	8	pF
C _{OUT}	IO Capacitance		10	pF

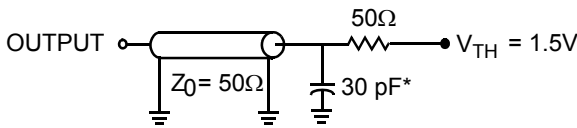
Thermal Resistance

Tested initially and after any design or process changes that may affect these parameters.

Parameter	Description	Test Conditions	119-Ball PBGA	Unit
Θ _{JA}	Thermal Resistance (junction to ambient)	Still air, soldered on a 3 × 4.5 inch, four layer printed circuit board	20.31	°C/W
Θ _{JC}	Thermal Resistance (junction to case)		8.35	°C/W

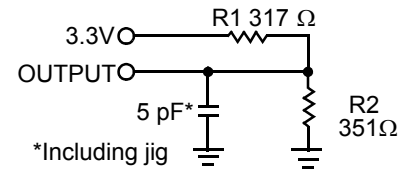
AC Test Loads and Waveforms

The AC test loads and waveform diagram follows. [4]

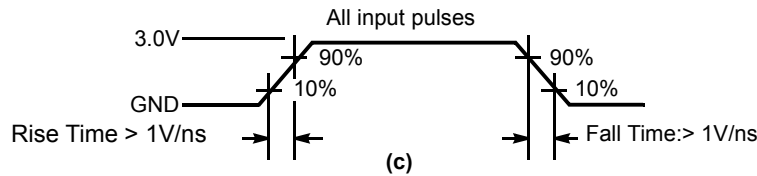


(a)

*Capacitive Load consists of all components of the test environment



(b)



(c)

Note

4. Valid SRAM operation does not occur until the power supplies have reached the minimum operating V_{DD} (3.0V). 100μs (t_{power}) after reaching the minimum operating V_{DD}, normal SRAM operation begins including reduction in V_{DD} to the data retention (V_{CCDR}, 2.0V) voltage.

AC Switching Characteristics

Over the Operating Range ^[5]

Parameter	Description	-8		Unit
		Min	Max	
Read Cycle				
$t_{power}^{[6]}$	V_{CC} (Typical) to the First Access	100		μs
t_{RC}	Read Cycle Time	8		ns
t_{AA}	Address to Data Valid		8	ns
t_{OHA}	Data Hold from Address Change	3		ns
t_{ACE}	\overline{CE} Active LOW to Data Valid ^[3]		8	ns
t_{DOE}	\overline{OE} LOW to Data Valid		5	ns
t_{LZOE}	\overline{OE} LOW to Low Z ^[7]	1		ns
t_{HZOE}	\overline{OE} HIGH to High Z ^[7]		5	ns
t_{LZCE}	\overline{CE} Active LOW to Low Z ^[3, 7]	3		ns
t_{HZCE}	\overline{CE} Deselect HIGH to High Z ^[3, 7]		5	ns
t_{PU}	\overline{CE} Active LOW to Power Up ^[3, 8]	0		ns
t_{PD}	\overline{CE} Deselect HIGH to Power Down ^[3, 8]		8	ns
Write Cycle ^[9, 10]				
t_{WC}	Write Cycle Time	8		ns
t_{SCE}	\overline{CE} Active LOW to Write End ^[3]	6		ns
t_{AW}	Address Setup to Write End	6		ns
t_{HA}	Address Hold from Write End	0		ns
t_{SA}	Address Setup to Write Start	0		ns
t_{PWE}	\overline{WE} Pulse Width	6		ns
t_{SD}	Data Setup to Write End	5		ns
t_{HD}	Data Hold from Write End	0		ns
t_{LZWE}	\overline{WE} HIGH to Low Z ^[7]	3		ns
t_{HZWE}	\overline{WE} LOW to High Z ^[7]		5	ns

Notes

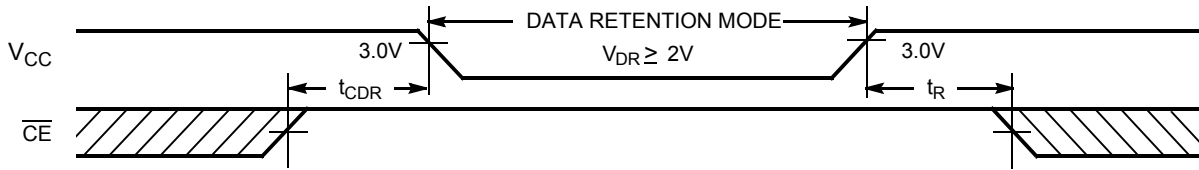
- Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5V, and input pulse levels of 0 to 3.0V. Test conditions for the read cycle use output loading as shown in part a) of [AC Test Loads and Waveforms](#), unless specified otherwise.
- t_{POWER} gives the minimum amount of time that the power supply is at typical V_{CC} values until the first memory access is performed.
- t_{HZOE} , t_{HZCE} , t_{HZWE} , t_{LZOE} , t_{LZCE} , and t_{LZWE} are specified with a load capacitance of 5 pF as in part (b) of [AC Test Loads and Waveforms](#). Transition is measured ± 200 mV from steady state voltage.
- These parameters are guaranteed by design and are not tested.
- The internal write time of the memory is defined by the overlap of \overline{CE}_1 or \overline{CE}_2 or \overline{CE}_3 LOW and \overline{WE} LOW. Chip enables must be active and \overline{WE} must be LOW to initiate a write. The transition of any of these signals terminate the write. The input data setup and hold timing are referenced to the leading edge of the signal that terminates the write.
- The minimum write cycle time for Write Cycle No. 3 (\overline{WE} controlled, \overline{OE} LOW) is the sum of t_{HZWE} and t_{SD} .

Data Retention Characteristics

Over the Operating Range

Parameter	Description	Conditions ^[3]	Min	Typ	Max	Unit
V _{DR}	V _{CC} for Data Retention		2			V
I _{CCDR}	Data Retention Current	V _{CC} = 2V, $\overline{CE} \geq V_{CC} - 0.2V$, V _{IN} ≥ V _{CC} - 0.2V or V _{IN} ≤ 0.2V			25	mA
t _{CDR} ^[11]	Chip Deselect to Data Retention Time		0			ns
t _R ^[12]	Operation Recovery Time		t _{RC}			ns

Data Retention Waveform



Switching Waveforms

Figure 2. Read Cycle No. 1 ^[13, 14]

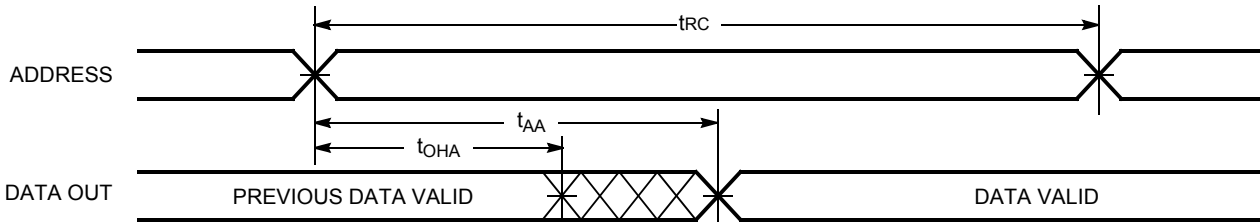
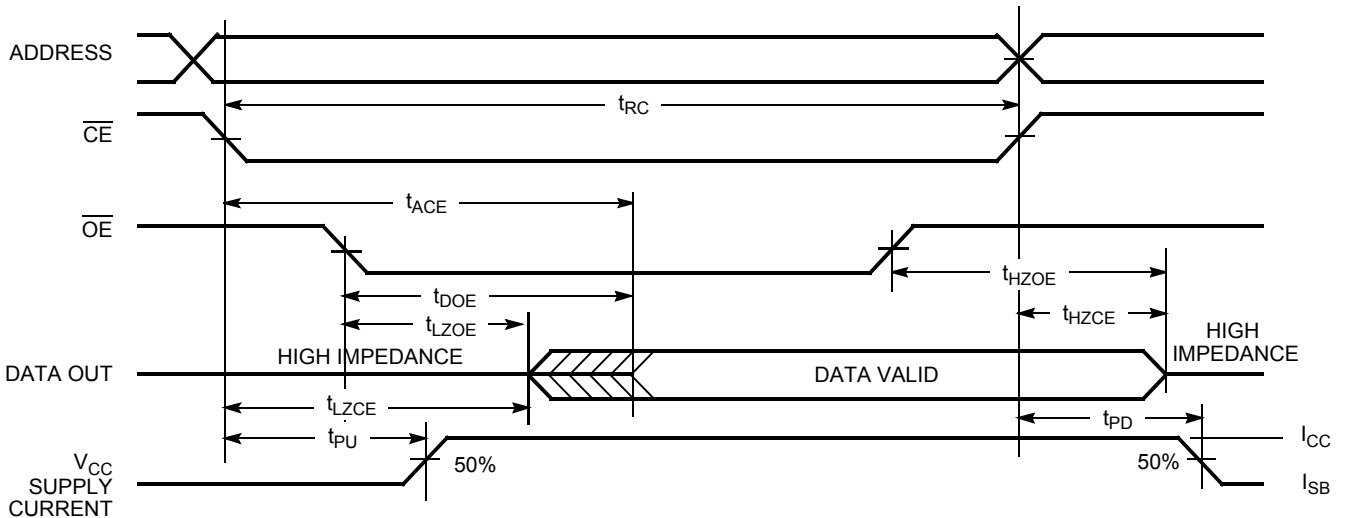


Figure 3. Read Cycle No. 2 (\overline{OE} Controlled) ^[3, 14, 15]



Notes

- 11. Tested initially and after any design or process changes that may affect these parameters.
- 12. Full device operation requires linear V_{CC} ramp from V_{DR} to V_{CC(min)} ≥ 50 μs or stable at V_{CC(min)} ≥ 50 μs.
- 13. Device is continuously selected. OE, CE = V_{IL}.
- 14. \overline{WE} is HIGH for read cycle.
- 15. Address valid before or similar to \overline{CE} transition LOW.

Switching Waveforms (continued)

Figure 4. Write Cycle No. 1 ($\overline{\text{CE}}$ Controlled) [3, 16, 17]

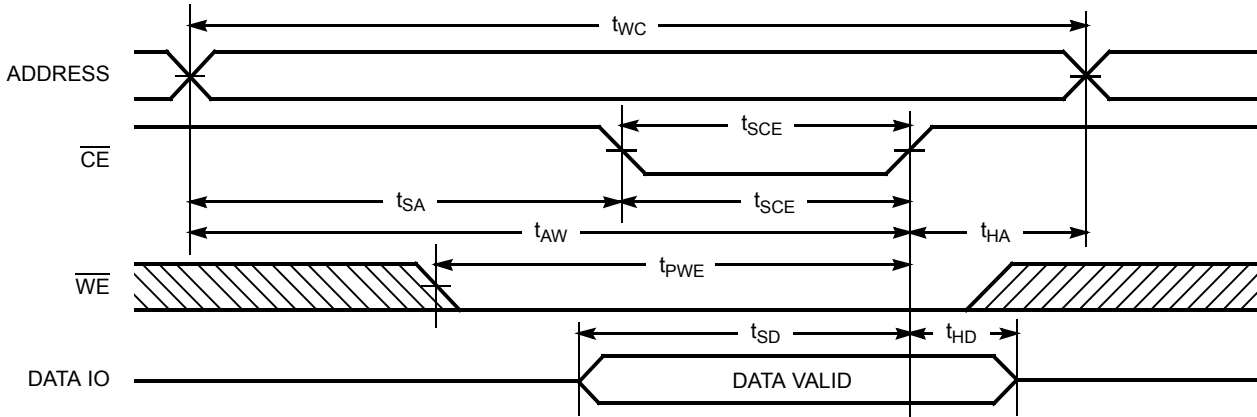


Figure 5. Write Cycle No. 2 ($\overline{\text{WE}}$ Controlled, $\overline{\text{OE}}$ HIGH During Write) [3, 16, 17]

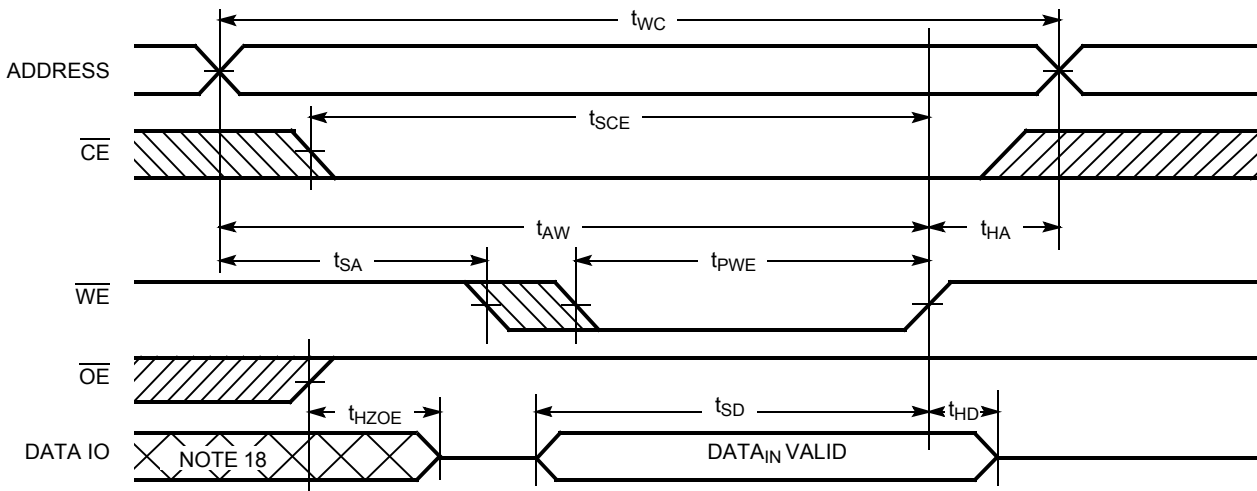
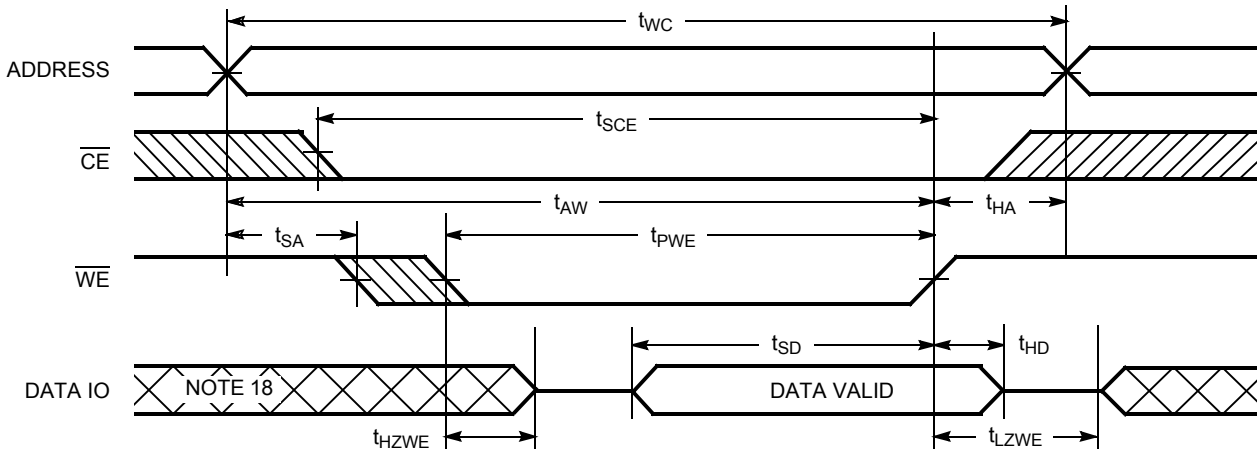


Figure 6. Write Cycle No. 3 ($\overline{\text{WE}}$ Controlled, $\overline{\text{OE}}$ LOW) [3, 17]



Notes

- 16. Data IO is high impedance if $\overline{\text{OE}} = V_{\text{IH}}$.
- 17. If CE goes HIGH simultaneously with WE going HIGH, the output remains in a high impedance state.
- 18. During this period, the IOs are in output state. Do not apply input signals.

Truth Table

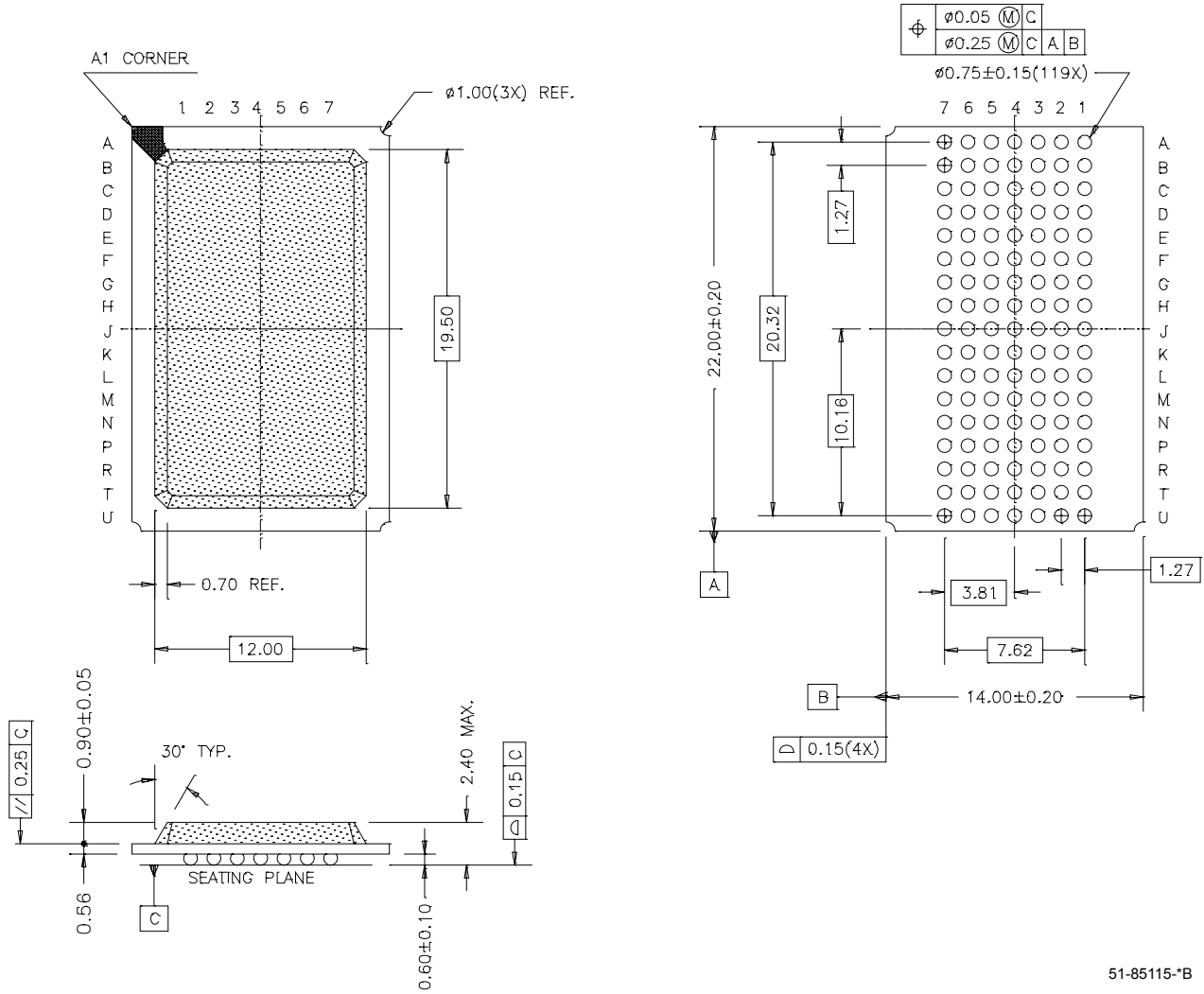
\overline{CE}_1	\overline{CE}_2	\overline{CE}_3	\overline{OE}	\overline{WE}	$IO_0 - IO_7$	$IO_8 - IO_{15}$	$IO_{16} - IO_{23}$	Mode	Power
H	H	H	X	X	High Z	High Z	High Z	Power Down	Standby (I_{SB})
L	H	H	L	H	Data Out	High Z	High Z	Read	Active (I_{CC})
H	L	H	L	H	High Z	Data Out	High Z	Read	Active (I_{CC})
H	H	L	L	H	High Z	High Z	Data Out	Read	Active (I_{CC})
L	L	L	L	H	Full Data Out	Full Data Out	Full Data Out	Read	Active (I_{CC})
L	H	H	X	L	Data In	High Z	High Z	Write	Active (I_{CC})
H	L	H	X	L	High Z	Data In	High Z	Write	Active (I_{CC})
H	H	L	X	L	High Z	High Z	Data In	Write	Active (I_{CC})
L	L	L	X	L	Full Data In	Full Data In	Full Data In	Write	Active (I_{CC})
L	L	L	H	H	High Z	High Z	High Z	Selected, Outputs Disabled	Active (I_{CC})

Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
8	CY7C1012DV33-8BGXC	51-85115	119-Ball Plastic Ball Grid Array (14 x 22 x 2.4 mm) (Pb-Free)	Commercial

Package Diagram

Figure 7. 119-Ball PBGA (14 x 22 x 2.4 mm)



51-85115-B

Document History Page

Document Title: CY7C1012DV33 12-Mbit (512K X 24) Static RAM				
Document Number: 38-05610				
REV.	ECN NO.	Issue Date	Orig. of Change	Description of Change
**	250650	See ECN	SYT	New datasheet
*A	469517	See ECN	NXR	Converted from Advance Information to Preliminary Corrected typo in the Document Title Removed -10 and -12 speed bins from product offering Changed J7 Ball of BGA from DNU to NC Removed Industrial Operating range from product offering Included the Maximum ratings for Static Discharge Voltage and Latch Up Current on page 3 Changed I _{CC(Max)} from 220 mA to 150 mA Changed I _{SB1(Max)} from 70 mA to 30 mA Changed I _{SB2(Max)} from 40 mA to 25 mA Specified the Overshoot specification in footnote 1 Updated the Truth Table Updated the Ordering Information table
*B	499604	See ECN	NXR	Added note 1 for NC pins Changed I _{CC} specification from 150 mA to 185 mA Updated Test Condition for I _{CC} in DC Electrical Characteristics table Added note for t _{ACE} , t _{LZCE} , t _{HZCE} , t _{PU} , t _{PD} , and t _{SCE} in AC Switching Characteristics Table on page 4
*C	1462585	See ECN	VKN	Converted from preliminary to final Updated block diagram Changed I _{CC} specification from 185 mA to 225 mA Updated thermal specs

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